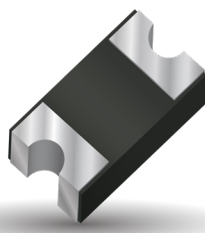


Schottky Barrier Rectifier Diode

Lead-less Chip Form



GENERAL DESCRIPTION

AVX Schottky rectifier diodes offer unique lead-less chip packaging technology which eliminates the lead frame wire bond to give the chip top-bottom symmetry for fewer mounting problems, better heat transfer, and current handling capability (compared to SOD devices).

FEATURES

- Lead-less Chip Form
- Low Vf
- High Current Capability
- Low Power Loss/High Efficiency
- UL 94V-0 Class Package Material
- Halogen Free

APPLICATIONS

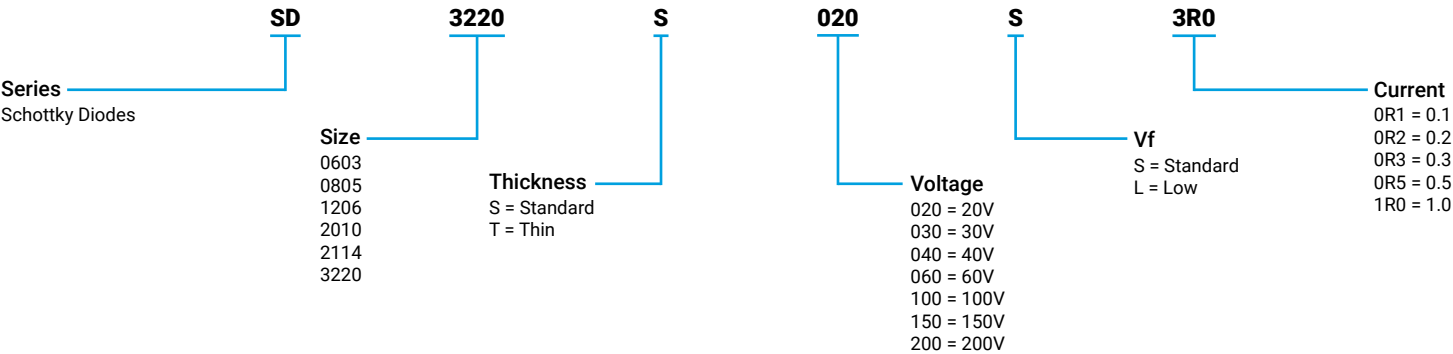
- Switch Mode Power Supplies
- High Frequency Rectification
- Portable Battery Powered Devices
- Reverse Bias Protection



MECHANICAL DATA

Case: FRP substrate with epoxy underfill
Terminations: 100% Sn plated (Pb-free), solderable per MIL-STD-750, Method 2026.
Operating Temperature: -55°C to 125°C
Storage Temperature: -55°C to 150°C

HOW TO ORDER



DIMENSIONS

Size (EIA)		Max Forward Current								
EIAJ	JEDEC	.1A	.2A	.3A	.5A	1A	2A	3A	5A	8A
0603	SOD-523									
0805	SOD-323									
1206	SOD-123									
2010	SMA (D0-214AC)									
2114	SMB (D0-214AA)									
3220	SMC (D0-214AB)									

Schottky Barrier Rectifier Diode

Lead-less Chip Form



ELECTRICAL CHARACTERISTICS

AVX PN	Size	Max Reverse Voltage	Max Forward Current	Max Peak Forward Surge Current	Reverse Current I_{RRM}		Forward Voltage V_f			Rth JA	Rth JL	Cj	Marking
		V_{RRM}	I_F	I_{FSM}	Typ	Max	I_F	Min	Max				
		V	A	A	mA	mA	A	V	V			pF	
SD3220S020S3R0	3220	20	3	100	0.025	0.5	3	0.47	0.5	55	17	180	3220 20S3
SD3220S040S3R0	3220	40	3	100	0.025	0.5	3	0.47	0.5	55	17	180	3220 40S3
SD3220S060S3R0	3220	60	3	100	0.025	0.5	3	0.65	0.7	55	17	180	3220 60S3
SD3220S100S3R0	3220	100	3	100	0.025	0.5	3	0.78	0.85	55	17	180	3220 100S3
SD3220S020S5R0	3220	20	5	130	0.045	0.5	5	0.52	0.55	55	17	180	3220 20S5
SD3220S040S5R0	3220	40	5	130	0.045	0.5	5	0.52	0.55	55	17	180	3220 40S5
SD3220S060S5R0	3220	60	5	130	0.045	0.5	5	0.65	0.7	55	17	180	3220 60S5
SD3220S100S5R0	3220	100	5	130	0.045	0.5	5	0.79	0.85	55	17	180	3220 100S5
SD2114S020S3R0	2114	20	3	80	0.04	0.5	3	0.48	0.5	55	17	180	2114 20S3
SD2114S040S3R0	2114	40	3	80	0.04	0.5	3	0.48	0.5	55	17	180	2114 40S3
SD2114S060S3R0	2114	60	3	80	0.04	0.5	3	0.65	0.7	55	17	180	2114 60S3
SD2114S100S3R0	2114	100	3	80	0.04	0.5	3	0.78	0.85	55	17	180	2114 100S3
SD2114S020S5R0	2114	20	5	105	0.045	0.5	5	0.5	0.55	55	17	250	2114 20S5
SD2114S040S5R0	2114	40	5	105	0.045	0.5	5	0.5	0.55	55	17	250	2114 40S5
SD2114S060S5R0	2114	60	5	105	0.045	0.5	5	0.65	0.7	55	17	250	2114 60S5
SD2114S100S5R0	2114	100	5	105	0.045	0.5	5	0.79	0.85	55	17	250	2114 100S5
SD2114S040S8R0	2114	40	8	135	0.045	0.5	8	0.53	0.55	55	17	450	2114 40S8

Schottky Barrier Rectifier Diode

Lead-less Chip Form



ELECTRICAL CHARACTERISTICS

AVX PN	Size	Max Reverse Voltage	Max Forward Current	Max Peak Forward Surge Current	Reverse Current I_{RRM}		Forward Voltage V_f			Rth JA	Rth JL	Cj	Marking
		V_{RRM}	I_F	I_{FSM}	Typ	Max	I_F	Min	Max				
		V	A	A	mA	mA	A	V	V			pF	
SD2010S020S1R0	2010	20	1	30	0.02	0.2	1	0.47	0.5	88	28	110	10S 20 1
SD2010S040S1R0	2010	40	1	30	0.02	0.2	1	0.47	0.5	88	28	110	10S 40 1
SD2010S060S1R0	2010	60	1	30	0.02	0.2	1	0.6	0.7	88	28	110	10S 60 1
SD2010S100S1R0	2010	100	1	30	0.02	0.2	1	0.76	0.85	88	28	110	10S 100 1
SD2010S150S1R0	2010	150	1	30	0.001	0.05	1	0.83	0.88	88	28	110	10S 150 1S
SD2010S200S1R0	2010	200	1	30	0.001	0.05	1	0.86	0.9	88	28	110	10S 200 1
SD2010S020S2R0	2010	20	2	50	0.025	0.2	2	0.49	0.5	75	17	115	10S 20 2
SD2010S040S2R0	2010	40	2	50	0.025	0.2	2	0.49	0.5	75	17	115	10S 40 2
SD2010S060S2R0	2010	60	2	50	0.025	0.2	2	0.6	0.7	75	17	115	10S 60 2
SD2010S100S2R0	2010	100	2	50	0.025	0.2	2	0.75	0.85	75	17	115	10S 100 2
SD2010S150S2R0	2010	150	2	50	0.001	0.2	2	0.83	0.88	88	28	110	10S 150 2
SD2010S200S2R0	2010	200	2	50	0.001	0.2	2	0.86	0.9	88	28	110	10S 200 2
SD2010S020S3R0	2010	20	3	80	0.02	0.2	3	0.46	0.5	86	24	120	10S 20 3
SD2010S040S3R0	2010	40	3	80	0.02	0.2	3	0.46	0.5	86	24	120	10S 40 3
SD2010S060S3R0	2010	60	3	80	0.02	0.2	3	0.58	0.7	86	24	120	10S 60 3
SD2010S100S3R0	2010	100	3	80	0.02	0.2	3	0.75	0.85	86	24	120	10S 100 3
SD2010S150S3R0	2010	150	3	80	0.001	0.05	3	0.83	0.88	88	28	110	10S 150 3

Schottky Barrier Rectifier Diode

Lead-less Chip Form



ELECTRICAL CHARACTERISTICS

AVX PN	Size	Max Reverse Voltage	Max Forward Current	Max Peak Forward Surge Current	Reverse Current I_{RRM}		Forward Voltage V_f			Rth JA	Rth JL	Cj	Marking
		V_{RRM}	I_F	I_{FSM}	Typ	Max	I_F	Min	Max				
		V	A	A	mA	mA	A	V	V			pF	
SD2010S200S3R0	2010	200	3	80	0.001	0.05	3	0.86	0.9	88	28	110	10S 200 3
SD2010S030S5R0	2010	30	5	80	–	0.2	3	0.42	0.44	55	17	210	10S 30 5
SD2010S020L1R0	2010	20	1	30	0.35	1	1	0.37	0.38	55	17	115	10L 20 1
SD2010S040L1R0	2010	40	1	30	0.35	1	1	0.37	0.38	55	17	115	10L 40 1
SD2010S020L2R0	2010	20	2	50	0.28	1	2	0.39	0.4	70	17	115	10L 20 2
SD2010S040L2R0	2010	40	2	50	0.28	1	2	0.39	0.4	70	17	115	10L 40 2
SD2010S020L3R0	2010	20	3	80	0.55	1	3	0.39	0.42	55	17	120	10L 20 3
SD2010S040L3R0	2010	40	3	80	0.55	1	3	0.39	0.42	55	17	120	10L 40 3
SD2010S030L3R0	2010	30	3	70	0.08	0.2	3	0.42	0.44	55	17	120	10L 30 3
SD1206S020S0R5	1206	20	0.5	15	0.01	0.05	0.5	0.4	0.42	88	28	120	B2
SD1206S040S0R5	1206	40	0.5	15	0.01	0.05	0.5	0.45	0.48	88	28	120	B4
SD1206S020S1R0	1206	20	1	20	0.015	0.2	1	0.46	0.5	88	28	110	A2
SD1206S040S1R0	1206	40	1	20	0.015	0.2	1	0.46	0.5	88	28	110	A4
SD1206S060S1R0	1206	60	1	20	0.015	0.2	1	0.62	0.7	88	28	110	A6
SD1206S100S1R0	1206	100	1	20	0.015	0.2	1	0.76	0.85	88	28	110	A10
SD1206S020S2R0	1206	20	2	40	0.03	0.2	2	0.47	0.5	75	17	115	L2
SD1206S040S2R0	1206	40	2	40	0.03	0.2	2	0.47	0.5	75	17	115	L4

Schottky Barrier Rectifier Diode

Lead-less Chip Form



ELECTRICAL CHARACTERISTICS

AVX PN	Size	Max Reverse Voltage	Max Forward Current	Max Peak Forward Surge Current	Reverse Current I_{RRM}		Forward Voltage V_f			Rth JA	Rth JL	Cj	Marking
		V_{RRM}	I_F	I_{FSM}	Typ	Max	I_F	Min	Max				
		V	A	A	mA	mA	A	V	V			pF	
SD1206S060S2R0	1206	60	2	40	0.03	0.2	2	0.58	0.7	75	17	115	L6
SD1206S100S2R0	1206	100	2	40	0.03	0.2	2	0.75	0.85	75	17	115	L10
SD1206S020L1R0	1206	20	1	25	0.3	1	1	0.37	0.38	88	28	115	A2L
SD1206S040L1R0	1206	40	1	25	0.3	1	1	0.37	0.38	88	28	115	A4L
SD1206S020L2R0	1206	20	2	40	0.28	1	2	0.39	0.4	70	22	115	L2L
SD1206S040L2R0	1206	40	2	40	0.28	1	2	0.39	0.4	70	22	115	L4L
SD1206T020S0R5	1206	20	0.5	15	0.01	0.05	0.5	0.4	0.42	88	28	120	B2S
SD1206T040S0R5	1206	40	0.5	15	0.01	0.05	0.5	0.45	0.48	88	28	120	B4S
SD1206T060S0R5	1206	60	0.5	15	0.01	0.05	0.5	0.48	0.55	88	28	120	B6S
SD1206T020S1R0	1206	20	1	20	0.015	0.2	1	0.46	0.5	88	28	110	A2S
SD1206T040S1R0	1206	40	1	20	0.015	0.2	1	0.46	0.5	88	28	110	A4S
SD1206T060S1R0	1206	60	1	20	0.015	0.2	1	0.62	0.7	88	28	110	A6S
SD1206T100S1R0	1206	100	1	20	0.015	0.2	1	0.76	0.85	88	28	110	A10S
SD1206T020S2R0	1206	20	2	40	0.03	0.2	2	0.47	0.5	75	17	115	L2S
SD1206T040S2R0	1206	40	2	40	0.03	0.2	2	0.47	0.5	75	17	115	L4S
SD1206T060S2R0	1206	60	2	40	0.03	0.2	2	0.58	0.75	75	17	115	L6S
SD1206T100S2R0	1206	100	2	40	0.03	0.2	2	0.75	0.85	75	17	115	L10S

Schottky Barrier Rectifier Diode

Lead-less Chip Form



ELECTRICAL CHARACTERISTICS

AVX PN	Size	Max Reverse Voltage	Max Forward Current	Max Peak Forward Surge Current	Reverse Current I_{RRM}		Forward Voltage V_f			Rth JA	Rth JL	Cj	Marking
		V_{RRM}	I_F	I_{FSM}	Typ	Max	I_F	Min	Max				
		V	A	A	mA	mA	A	V	V			pF	
SD1206T040S3R0	1206	40	3	40	0.03	0.2	3	0.53	0.55	88	28	110	K4S
SD1206T060S3R0	1206	60	3	40	0.03	0.2	3	0.75	0.8	88	28	110	K6S
SD1206T020L1R0	1206	20	1	25	0.3	1	1	0.37	0.38	88	28	115	A2 LS
SD1206T040L1R0	1206	40	1	25	0.3	1	1	0.37	0.38	88	28	115	A4 LS
SD0805S020S0R1	805	20	0.1	2	0.004	0.03	0.1	0.38	0.45	160	110	18	F 2
SD0805S040S0R1	805	40	0.1	2	0.004	0.03	0.1	0.4	0.5	160	110	18	F 4
SD0805S020S0R2	805	20	0.2	2	0.008	0.05	0.2	0.42	0.45	160	110	15	D 2
SD0805S040S0R2	805	40	0.2	2	0.008	0.05	0.2	0.45	0.5	160	110	15	D 4
SD0805S020S0R3	805	20	0.3	2	0.008	0.05	0.3	0.47	0.5	160	110	30	C 2
SD0805S040S0R3	805	40	0.3	2	0.008	0.05	0.3	0.47	0.5	160	110	30	C 4
SD0805S020S0R5	805	20	0.5	5	0.015	0.1	0.5	0.4	0.44	120	28	28	B 2
SD0805S030S0R5	805	30	0.5	5	0.015	0.1	0.5	0.4	0.46	120	28	28	B 3
SD0805S040S0R5	805	40	0.5	5	0.015	0.1	0.5	0.4	0.48	120	28	28	B 4
SD0805S020S1R0	805	20	1	10	0.028	0.2	1	0.42	0.45	120	28	115	A 2
SD0805S040S1R0	805	40	1	10	0.008	0.05	1	0.49	0.55	88	28	110	A 41
SD0805S060S1R0	805	60	1	10	0.028	0.2	1	0.62	0.65	120	28	115	A 6
SD0805S020L1R0	805	20	1	10	0.3	1	1	0.37	0.38	88	28	115	A 2L

Schottky Barrier Rectifier Diode

Lead-less Chip Form

ELECTRICAL CHARACTERISTICS

AVX PN	Size	Max Reverse Voltage	Max Forward Current	Max Peak Forward Surge Current	Reverse Current I_{RRM}		Forward Voltage V_f			Rth JA	Rth JL	Cj	Marking
		V_{RRM}	I_F	I_{FSM}	Typ	Max	I_F	Min	Max				
		V	A	A	mA	mA	A	V	V			pF	
SD0805S040L1R0	805	40	1	10	0.3	1	1	0.37	0.38	88	28	115	A 4L
SD0603S020S0R1	603	20	0.1	2	0.008	0.05	0.1	0.38	0.4	160	110	30	2F
SD0603S040S0R1	603	40	0.1	2	0.008	0.05	0.1	0.38	0.4	160	110	30	4F
SD0603S020S0R2	603	20	0.2	2	0.008	0.05	0.2	0.43	0.45	160	110	35	2D
SD0603S040S0R2	603	40	0.2	2	0.0005	0.001	0.2	0.43	0.45	160	110	35	4D
SD0603S020S0R3	603	20	0.3	2	0.008	0.05	0.3	0.47	0.5	160	110	35	2C
SD0603S040S0R3	603	40	0.3	2	0.008	0.05	0.3	0.47	0.5	160	110	35	4C

Schottky Barrier Rectifier Diode
Lead-less Chip Form



PAD LAYOUT mm (inches)

0603 Diagram showing the pad layout for the 0603 package. Dimensions include: 0.80 (0.031) MIN. for the left pad width, 0.60 (0.024) MIN. for the left pad thickness, 1.10 (0.043) MAX. for the right pad width, and 2.30 (0.091) REF. for the total width.	2010 Diagram showing the pad layout for the 2010 package. Dimensions include: 1.47 (0.058) MIN. for the left pad width, 1.27 (0.050) MIN. for the left pad thickness, 2.60 (0.102) MAX. for the right pad width, and 5.14 (0.202) REF. for the total width.
0805 Diagram showing the pad layout for the 0805 package. Dimensions include: 0.90 (0.035) MIN. for the left pad width, 0.80 (0.031) MIN. for the left pad thickness, 1.30 (0.051) MAX. for the right pad width, and 2.90 (0.114) REF. for the total width.	2114 Diagram showing the pad layout for the 2114 package. Dimensions include: 3.00 (0.118) MIN. for the left pad width, 2.65 (0.104) MAX. for the right pad width, and 6.65 (0.262) REF. for the total width.
1206 1206-T Diagram showing the pad layout for the 1206 package. Dimensions include: 1.50 (0.059) MIN. for the left pad width, 1.0 (0.039) MIN. for the left pad thickness, 2.00 (0.787) MAX. for the right pad width, and 4.0 (0.157) REF. for the total width.	3220 Diagram showing the pad layout for the 3220 package. Dimensions include: 3.90 (0.154) MIN. for the left pad width, 4.10 (0.161) MAX. for the right pad width, and 11.9 (0.469) REF. for the total width.

Schottky Barrier Rectifier Diode

Lead-less Chip Form

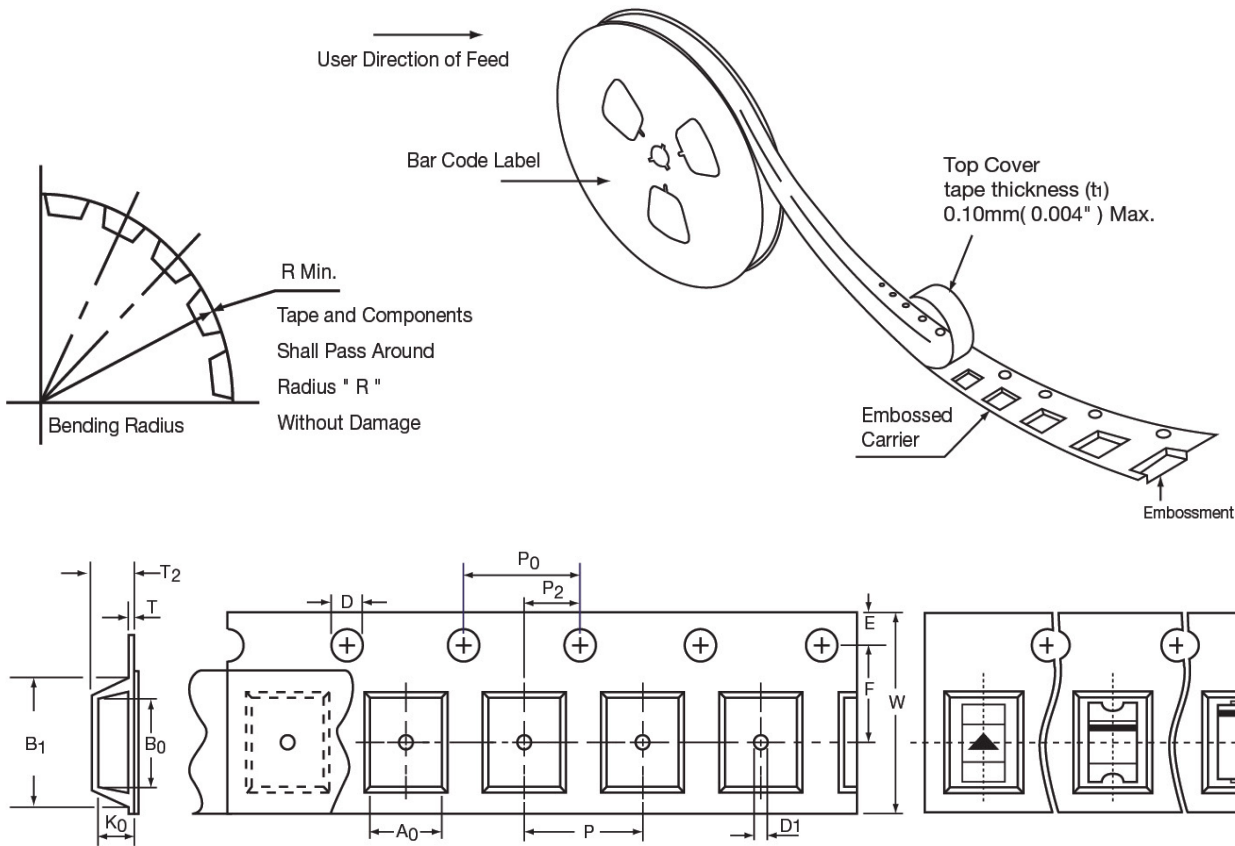
PAD LAYOUT mm (inches)

0603 SOD-523	2010 SMA (DO-214AC)
0805 SOD-323	2114 SMB (DO-214AA)
1206 SOD-123	3220 SMC (DO-214AB)
1206-T SOD-323	Polarity: Laser Cathode Band Marking

Schottky Barrier Rectifier Diode

Lead-less Chip Form

CARRIER TAPE



REEL DIMENSIONS mm inches

Tape Size	D	E	P ₀	A ₀	B ₀	K ₀	T max	P ₂
8, 12 mm	1.50 ± 0.1 (0.059 ± 0.004)	1.75 ± 0.1 (0.069 ± 0.004)	4.0 ± 0.1 (0.157 ± 0.004)	See Note 1			0.4 -0.016	2.0 ± 0.1 (0.079 ± 0.002)
16 mm	1.55 ± 0.05 (0.061 ± 0.002)	1.75 ± 0.1 (0.069 ± 0.004)	4.0 ± 0.1 (0.157 ± 0.004)					

Product Size	Tape Size	B1	D1	F	P	W	T2	R Min
0603	8mm	2.0 max (0.079 max)	0.80 ± 0.05 (0.031 ± 0.002)	3.50 ± 0.05 (0.138 ± 0.002)	4.00 ± 0.10 (0.157 ± 0.004)	8.00 ± 0.30 (0.315 ± 0.012)	1.00 ± 0.10 (0.039 ± 0.004)	25 -0.98
0805							1.22 ± 0.10 (0.048 ± 0.004)	
1206	12mm	8.2 max 0.323 max)	1.50 min. (0.059 min.)	5.50 ± 0.05 (0.217 ± 0.002)	8.00 ± 0.10 (0.315 ± 0.004)	12.00 ± 0.30 (0.472 ± 0.012)	1.75 ± 0.1 (0.069 ± 0.004)	30 -1.181
1206-S							1.40 ± 0.1 (0.055 ± 0.004)	
2010							1.51 ± 0.10 (0.059 ± 0.004)	
2114							1.65 ± 0.10 (0.065 ± 0.004)	
3220	16mm	12.1 max (0.476 max)	7.50 ± 0.10 (0.295 ± 0.004)	7.50 ± 0.10 (0.295 ± 0.004)	8.00 ± 0.10 (0.315 ± 0.004)	16.00 ± 0.30 (0.630 ± 0.012)	2.50 max (0.098 max)	40 -1.575

NOTES:

- A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm (0.002") Min. to 0.50 mm (0.02") Max. for 8mm tape, and 0.15mm (0.066") Min. to 0.90 mm (0.035") Max. 12 mm tape.
- All surface mount components are packed in accordance with EIA standard 481-1 and 481-2

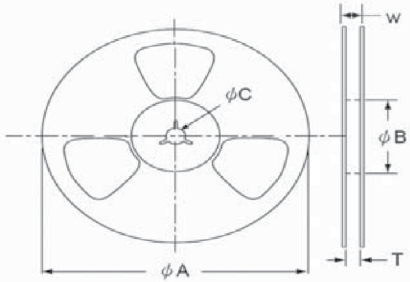
Schottky Barrier Rectifier Diode

Lead-less Chip Form



REEL DIMENSIONS mm inches

Symbol	Tape Size	φA	φB	φC	W	T
0603	8	178 ± 2.0	60 ± 0.5	13.5 ± 0.5	12.0 ± 0.5	9.0 ± 0.5
0805	-0.315	(7.008 ± 0.079)	(2.362 ± 0.020)	(0.532 ± 0.020)	(0.472 ± 0.020)	(0.354 ± 0.020)
1206	12 -0.472	178 ± 2.0	50 min (1.969 min)	13.0 ± 0.5 (0.512 ± 0.020)	18.7 max (0.736 max)	14.4 max (0.567 max)
1206-T		(7.008 ± 0.079)				
2010		330 ± 2.0 (12.99 ± 0.079)				
2114						
3220	16 -0.63				22.7 max (0.893 max)	18.4 max (0.724 max)



QUANTITIES

Size	Reel Size	Qty/Reel
0603	7"	3,000
0805		
1206	7"	3,000
1206-T		
2010		
2114	13"	5,000
3220	13"	3,000